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DERWENT-WEEK: 200316

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TITLE: Structure of heat sink of semiconductor
assembly and
fabricating method thereof

INVENTOR: LEE, M G; YOON, S Y

PATENT-ASSIGNEE: SSI[SSISN]

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PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE
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APPLICATION-DATA:

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INT-CL (IPC): H01L023/36

ABSTRACTED-PUB-NO: KR2002068208A

BASIC-ABSTRACT:

NOVELTY - A method for fabricating a structure of a heat sink of a semiconductor assembly is provided to shorten the length of a wire and to increase a heat radiating area, by forming each heat sink of a base frame on which a chip or die is settled and by forming a plurality of grooves in the lower portion of each heat sink.

DETAILED DESCRIPTION - A chip settling part(120) and a coupling part(130) of the base frame are determined. The coupling part which is the periphery of the chip settling part is etched to have a predetermined height. The

lower portion
of the bottom surface of the chip settling part is etched to form a plurality
of heat radiating grooves(140). The outer surface of each coupling
part of the
base frame is pressed and cut while a plurality of supporting bars
are formed.
The upper portion of the chip settling part is plated to complete
each heat
sink on the base frame.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: STRUCTURE HEAT SINK SEMICONDUCTOR ASSEMBLE FABRICATE
METHOD

DERWENT-CLASS: U11 V04

EPI-CODES: U11-D02B1; V04-T03A; V04-T03Q;

